

REMARKS


In this Amendment After Final, Applicants have amended independent Claims 1 and 7 to recite that the second semiconductor region is characterized by a dopant concentration less than $1 \times 10^{18}/\text{cm}^3$. Claim 1 previously recited a dopant concentration less than $1 \times 10^{19}/\text{cm}^3$, and U.S. Patent Application Publication No. 2002/0045342 to Hu et al., the primary reference in the 35 U.S.C. § 103(a) rejections, was cited for teaching a dopant concentration level of between $1 \times 10^{18}/\text{cm}^3$ and $5 \times 10^{21}/\text{cm}^3$. Because the independent claims now recite a dopant concentration level that is clearly not taught by the applied art, Applicants respectfully submit that the 35 U.S.C. § 103(a) rejections against the claims should be withdrawn. It is important to note that these amendments are being made merely to expedite the prosecution of this application and should not be interpreted as an acquiescence of the correctness of the rejections. Indeed, Applicants still submit that the rejections of the claims are improper for at least the reasons stated in its prior response.

In view of the foregoing amendments and remarks, Applicants submit that this application is in condition for allowance. Reconsideration is respectfully requested. If the Examiner has any questions concerning this Amendment, he is asked to contact the undersigned attorney at (312) 321-4719.

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Respectfully submitted,

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